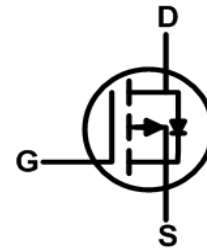




- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

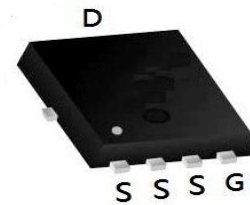


### Description

The WLQ3419A is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WLQ3419A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### PDFN3333-8L Pin Configuration



### Product Summary

BVDSS	RDSON	ID
-30V	8.5 mΩ	-55A

### Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V <sub>DSS</sub>	Drain-Source Voltage	-30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> = 25°C	-55
		T <sub>C</sub> = 100°C	-23
I <sub>DM</sub>	Pulsed Drain Current <sup>note1</sup>	-140	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy <sup>note2</sup>	78.8	mJ
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> = 25°C	21.5
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	5.8	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D = -250\mu A$	-30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V,$	-	-	-1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS} = -10V, I_D = -12A$	-	8.5	11	m $\Omega$
		$V_{GS} = -4.5V, I_D = -8A$	-	13	18	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	2800	-	pF
$C_{oss}$	Output Capacitance		-	346	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	319	-	pF
$Q_g$	Total Gate Charge	$V_{DS} = -15V, I_D = -20A,$ $V_{GS} = -10V$	-	30	-	nC
$Q_{gs}$	Gate-Source Charge		-	5.3	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	7.6	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15V, I_D = -20A,$ $V_{GS} = -10V, R_{GEN} = 2.5\Omega$	-	14	-	ns
$t_r$	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	95	-	ns
$t_f$	Turn-off Fall Time		-	65	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-140	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = -35A$	-	-0.8	-1.2	V

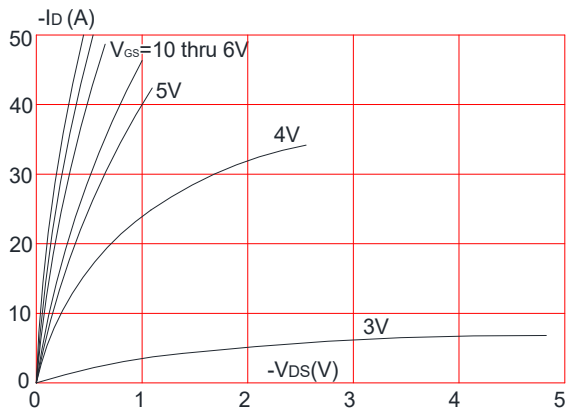
Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition:  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = -20V$ ,  $V_G = -10V$ ,  $L = 0.5mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -17A$ 3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$

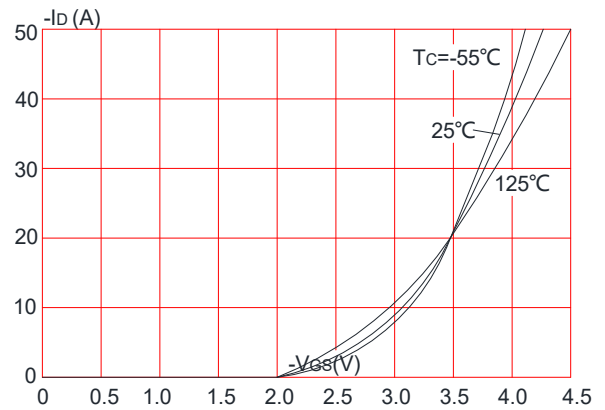


### Typical Performance Characteristics

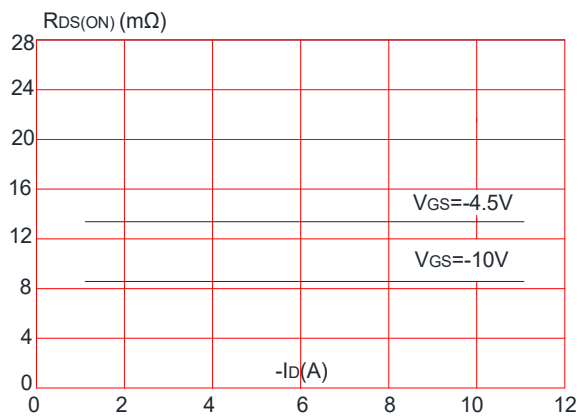
**Figure 1:** Output Characteristics



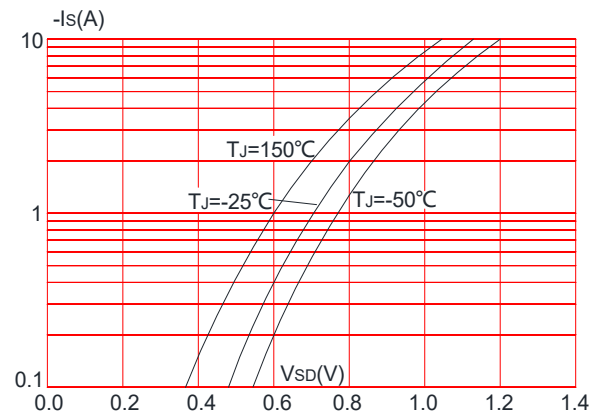
**Figure 2:** Typical Transfer Characteristics



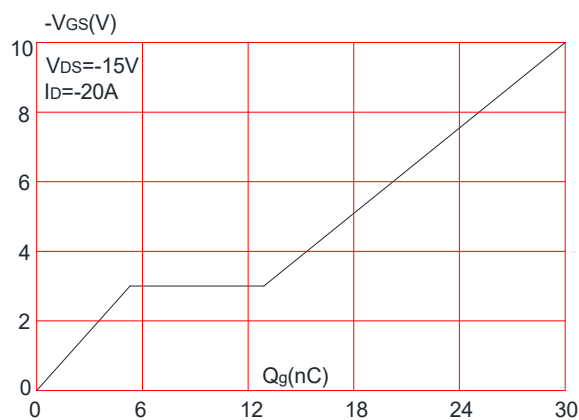
**Figure 3:** On-resistance vs. Drain Current



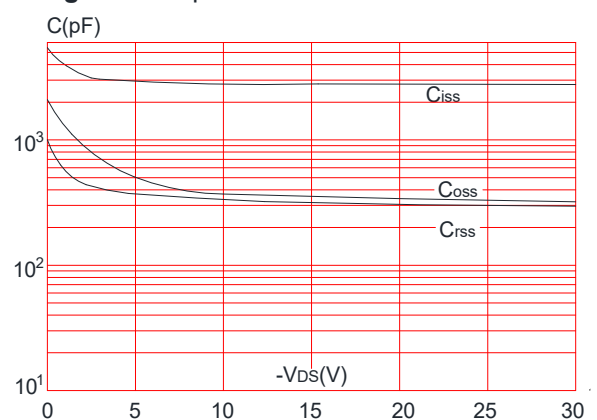
**Figure 4:** Body Diode Characteristics



**Figure 5:** Gate Charge Characteristics

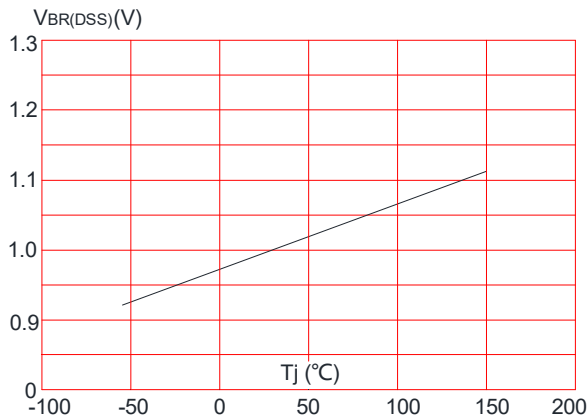


**Figure 6:** Capacitance Characteristics

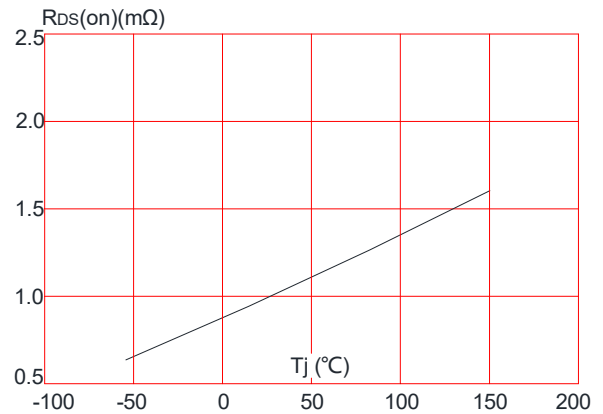




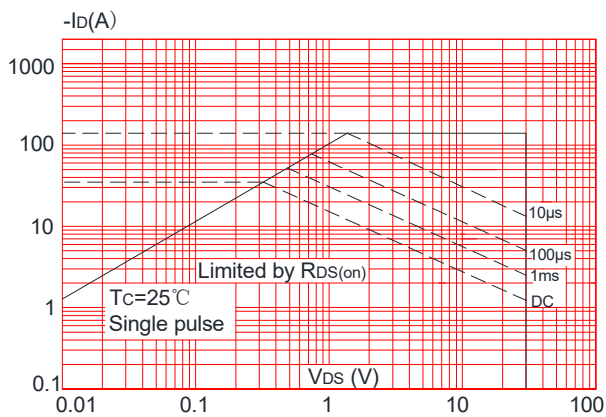
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



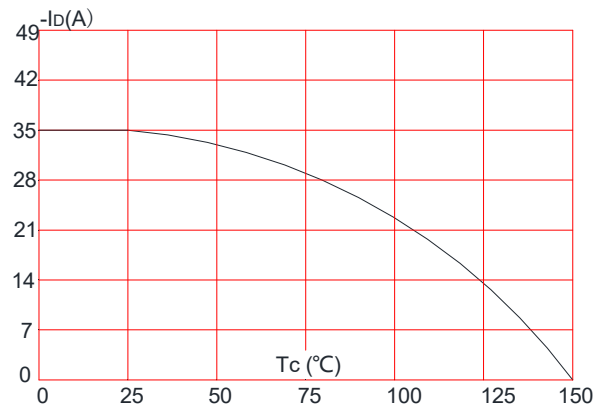
**Figure 8:** Normalized on Resistance vs. Junction Temperature



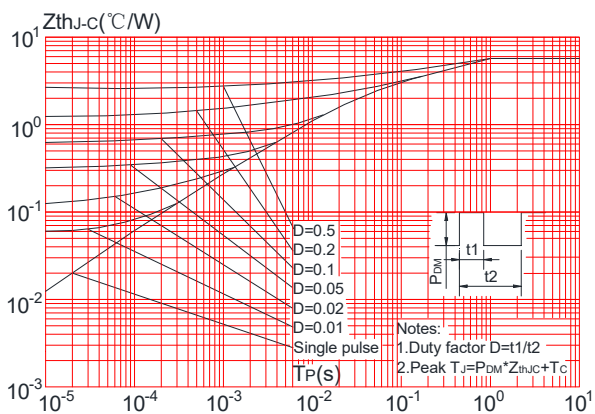
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

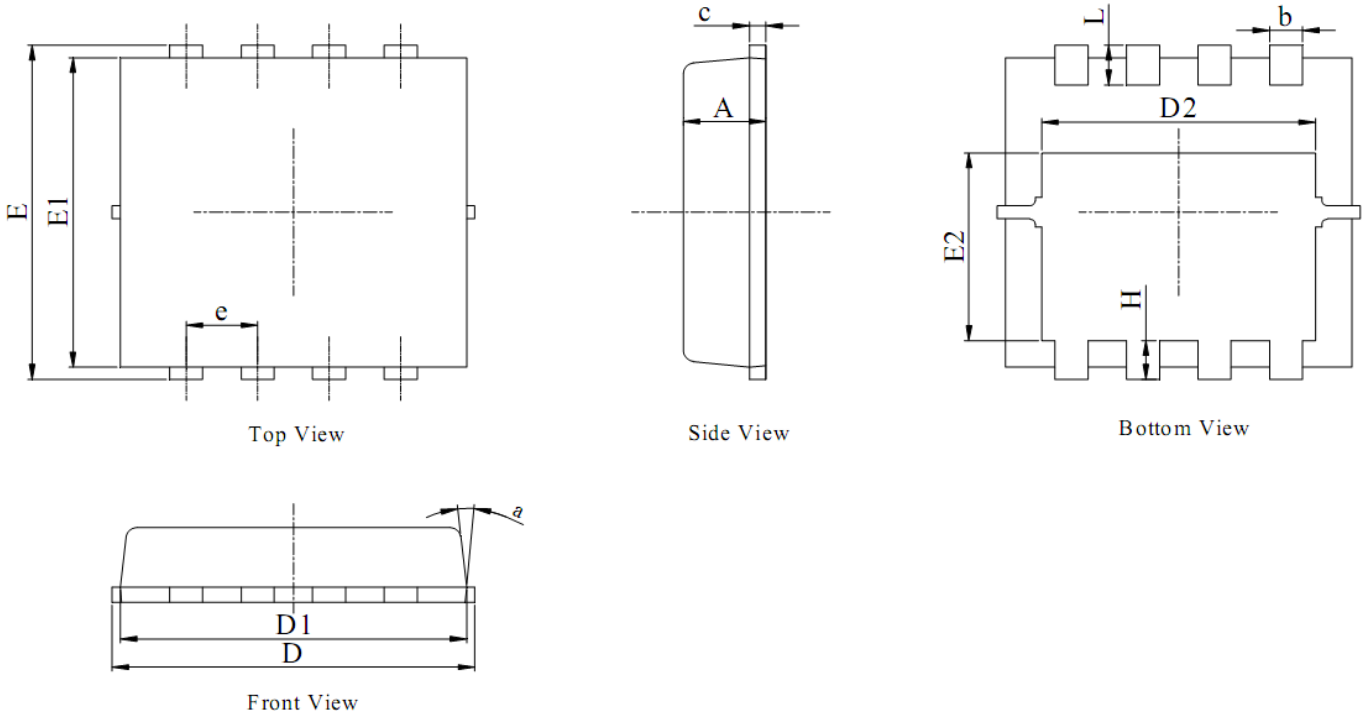


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





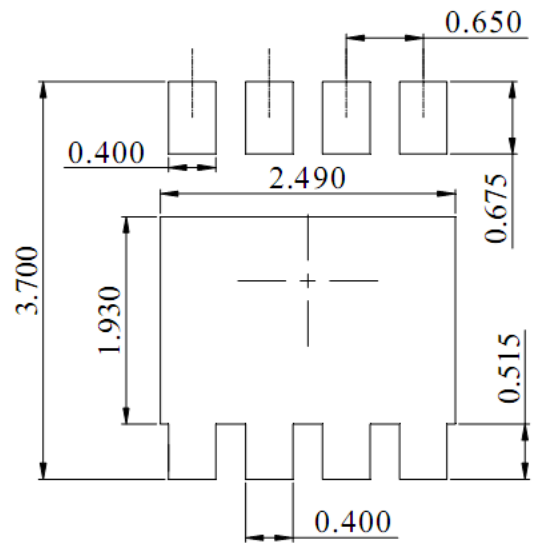
Package Mechanical Data-PDFN3333-8L-Single



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS



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